杰力科技股份有限公司
Excelliance MOS Corporation

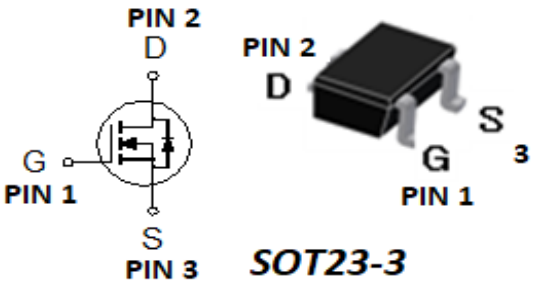
EMBA2N10JSS

Single N-Channel Logic Level Enhancement Mode Field Effect Transistor

▪Product Summary:

	N-CH
BVDSS	100V
$R_{DSON\ (MAX.)}$@V_{GS}=10V	100mΩ
$R_{DSON\ (MAX.)}$@V_{GS}=4.5V	150mΩ
I_D @T_A=25℃	2A
I_D @T_A=70℃	2A

▪ Pin Description:



Single N Channel MOSFET
UIS, Rg 100% Tested
Pb-Free Lead Plating & Halogen Free

▪ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	2	A
	T_A = 70 °C		2	
Pulsed Drain Current[1]		I_{DM}	8	
Avalanche Current		I_{AS}	2	
Avalanche Energy	L = 1mH	EAS	2	mJ
Repetitive Avalanche Energy[2]	L = 0.5mH	EAR	1	
Power Dissipation	T_A = 25 °C	P_D	1	W
	T_A = 70 °C		0.7	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

▪ 100% UIS testing in condition of VD=30V, L=0.1mH, VG=10V, IL=0.6A, Rated VDS=100V N-CH

▪THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Ambient[3]	$R_{\theta JA}$		120	°C/W
	RθJA(t≦10s)		80	

[1]Pulse width limited by maximum junction temperature.
[2]Duty cycle < 1%
[3]120°C / W when mounted on a 1 in^2 pad of 2 oz copper.
[4]Guarantee by Engineering test

▪ **ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage[4]	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250uA	100			V
Gate Threshold Voltage[4]	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	1.2	1.9	2.5	
Gate-Body Leakage[4]	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current[4]	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	uA
		V_{DS} =70V, V_{GS} =0V, T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	2			A
Drain-Source On-State Resistance[1,4]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 8A		75	100	mΩ
		V_{GS} = 4.5V, I_D = 5A		100	150	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 8A		8		S
DYNAMIC						
Input Capacitance[5]	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		221		pF
Output Capacitance[5]	C_{oss}			93		
Reverse Transfer Capacitance[5]	C_{rss}			28		
Gate Resistance[4,5]	R_g	f = 1MHz		1.0		Ω
Total Gate Charge[1,2,5]	Q_g(V_{GS}=10V)	VDS = 80V, VGS = 10V, ID = 8A		6.5		nC
Gate-Source Charge[1,2,5]	Q_{gs}			1.3		
Gate-Drain Charge[1,2,5]	Q_{gd}			2.2		
Turn-On Delay Time[1,2,5]	$t_{d(on)}$	VDS = 50V, VGS = 10V, ID =5A , Rg = 3Ω		4.6		nS
Rise Time[1,2,5]	t_r			6.8		
Turn-Off Delay Time[1,2,5]	$t_{d(off)}$			10		
Fall Time[1,2,5]	t_f			8.6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Current	I_S				2	A
Pulsed Current[3]	I_{SM}				8	
Forward Voltage[1,4]	V_{SD}	I_F = 1A, V_{GS} = 0V			1.3	V
Reverse Recovery Time[5]	t_{rr}	I_F = 18A, dI_F/dt = 100A / uS		22		nS
Peak Reverse Recovery Current[5]	$I_{RM(REC)}$			1.1		A
Reverse Recovery Charge[5]	Q_{rr}			13		nC

[1]Pulse test : Pulse Width ≦ 300 usec, Duty Cycle ≦ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

[4]Guarantee by FT test Item

[5]Guarantee by Engineering test

EMC will review datasheet by quarter, and update new version.

▪TYPICAL CHARACTERISTICS

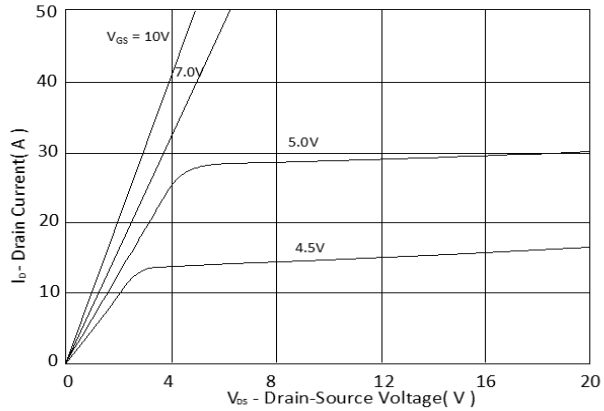


Fig.1 Typical Output Characteristics

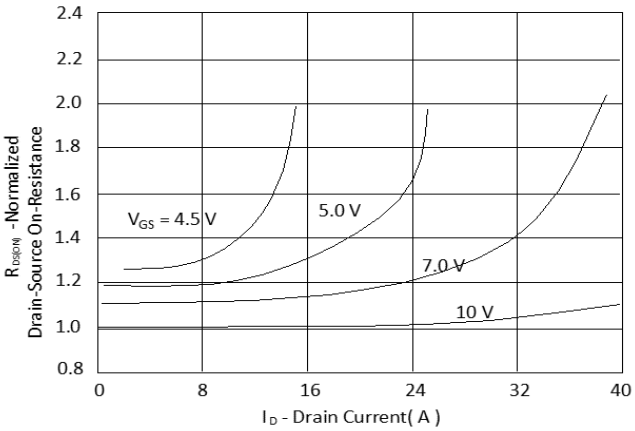


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

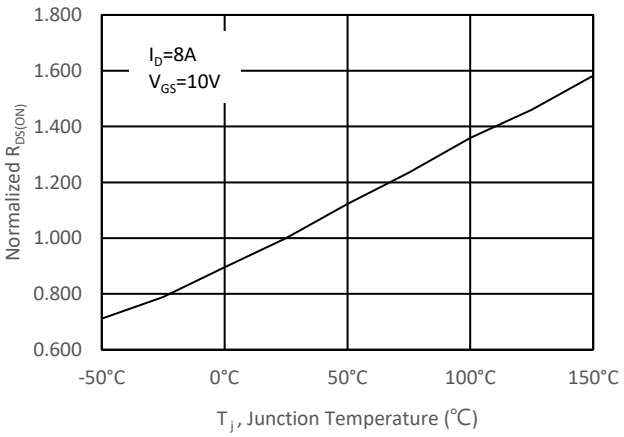


Fig.3 Normalized On-Resistance v.s. Junction Temperature

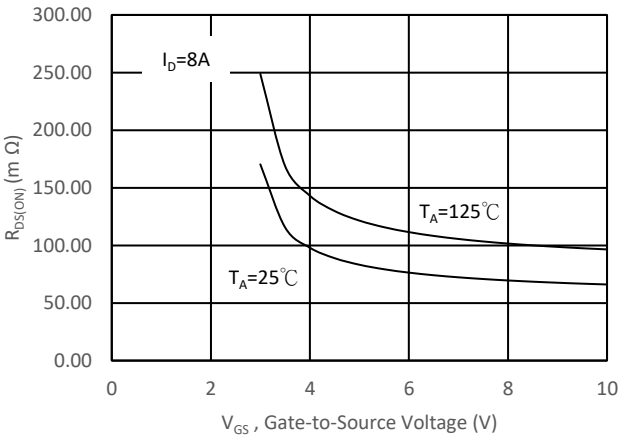


Fig.4 On-Resistance v.s. Gate Voltage

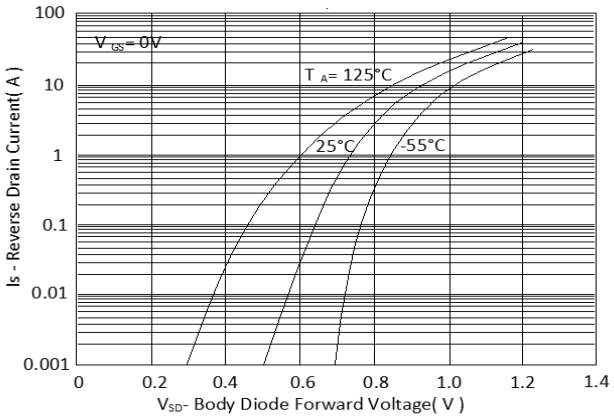


Fig.5 Forward Characteristic of Reverse Diode

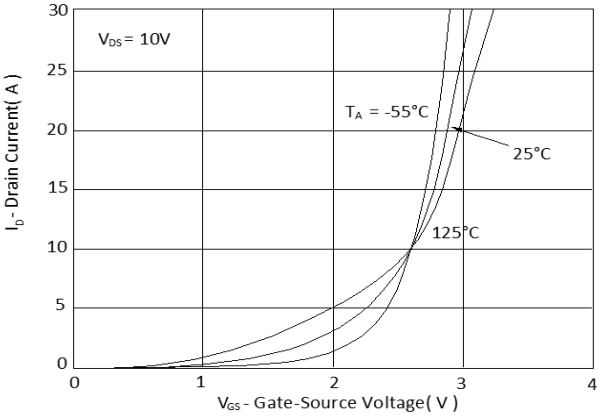


Fig.6 Transfer Characteristics

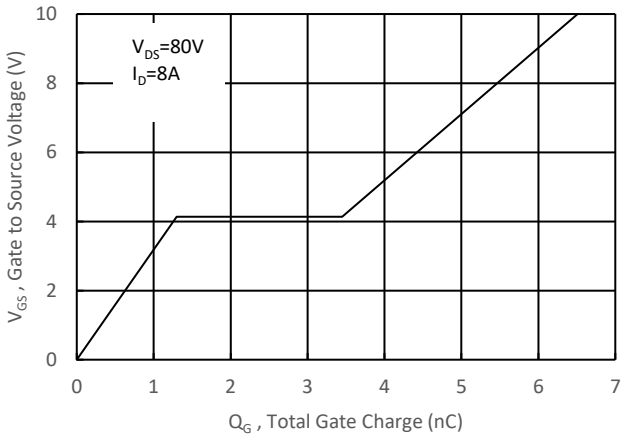


Fig.7 Gate Charge Characteristics

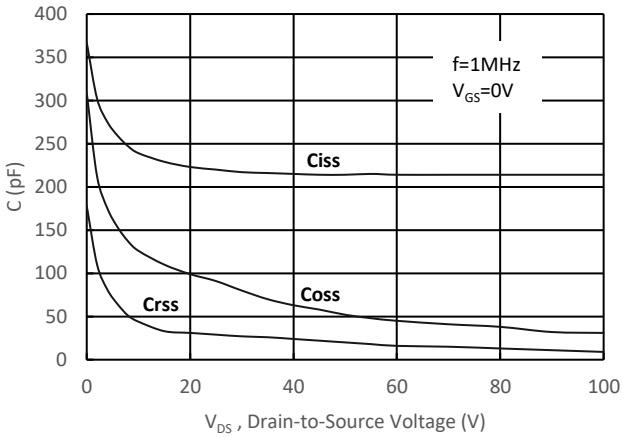


Fig.8 Typical Capacitance Characteristics

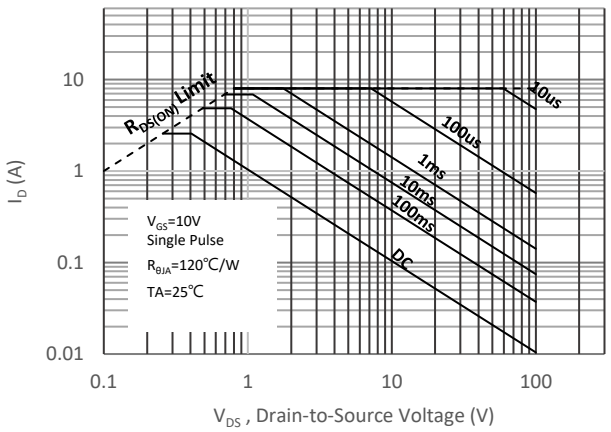


Fig 9. Maximum Safe Operating Area

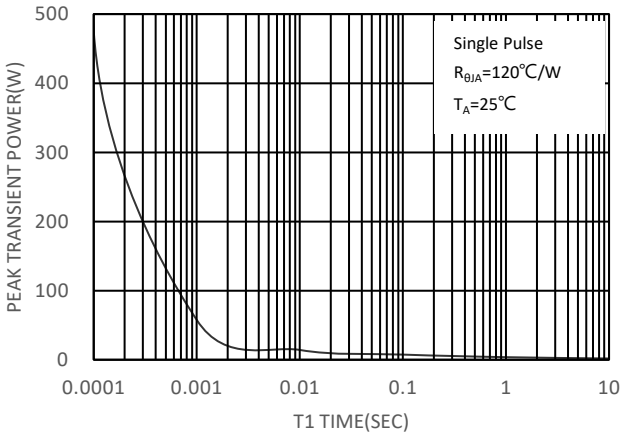


Fig 10. Single Pulse Maximum Power Dissipation

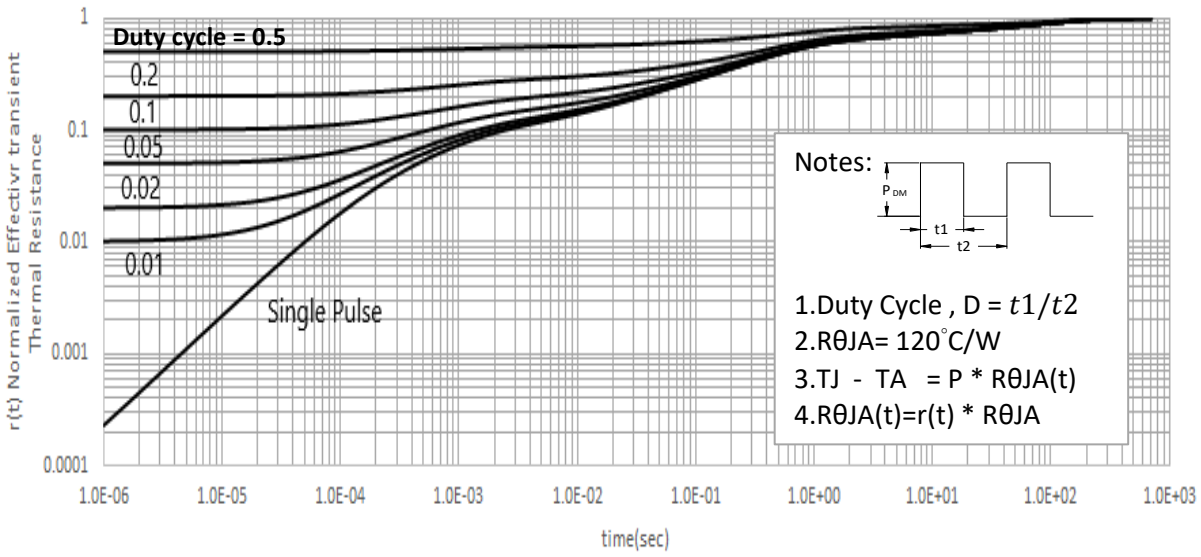
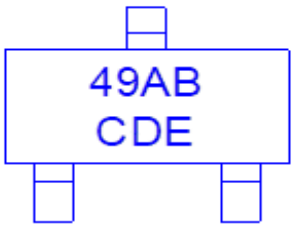


Fig 11. Effective Transient Thermal Impedance

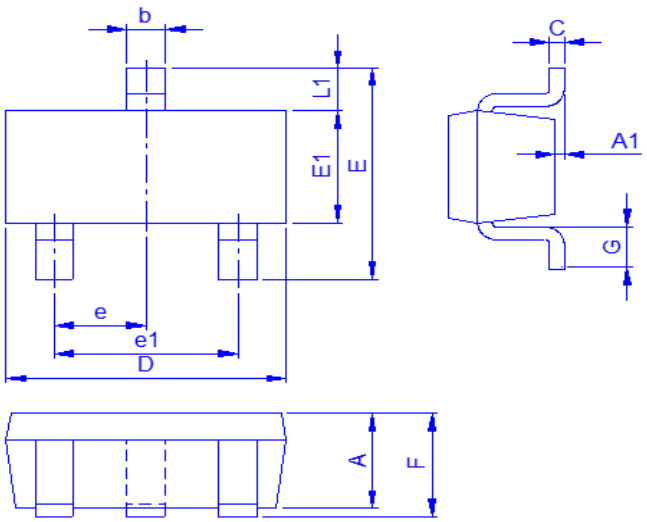
Ordering & Marking Information:

Device Name: EMBA2N10JSS for SOT-23-3



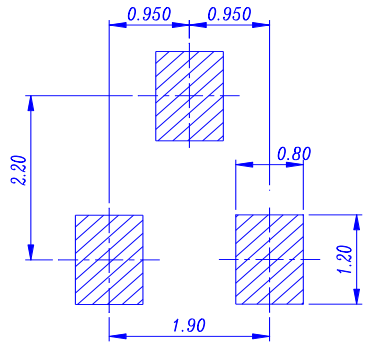
49 : Device Code, 49 for EMBA2N10JSS
A: Year(A:2008 B:2009 C:2010….)
B: Month(A:01 B:02 C:03 D:04 E:05 F:06
G:07 H:08 I:09 J:10 K:11 L:12)
CDE: Serial No.

Outline Drawing

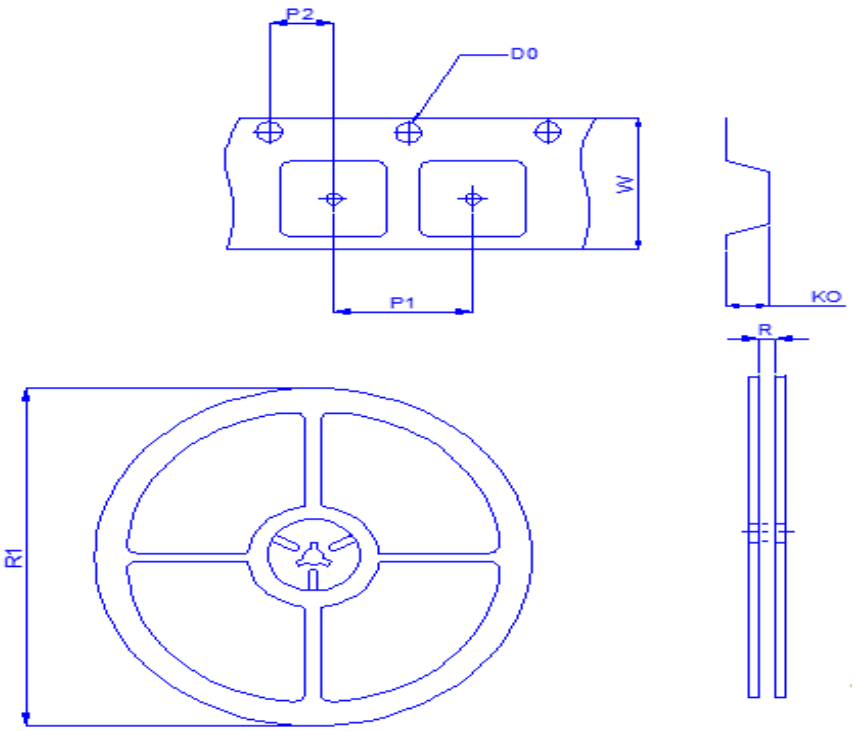


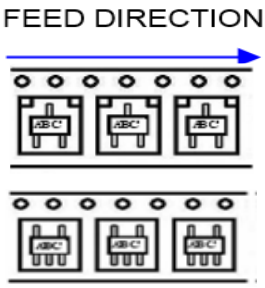
	A	A1	b	C	D	E	E1	e	e1	F	G	L1
Min.	0.88	0	0.3	0.08	2.8	2.1	1.2	0.9	1.8	0.89	0.3	0
Typ.	0.95	0	0	0	2.9	2.5	1.3	0.95	1.9	0	0	0.54
Max.	1.1	0.1	0.5	0.202	3.04	2.64	1.4	1	2	1.2	0.6	0

Footprint



◆ **Tape&Reel Information:3000pcs/Reel (Dimension in millimeter)**



產品別	SOT23-3
Reel尺寸	7"
編帶方式	

Dimension in mm

Dimension	Carrier tape					Reel	
	D0	K0	P1	P2	W	R	R1
Typ.	1.53	1.45	4	2	8	8.5	178
±	0.2	0.5	0.2	0.2	0.5	REF	REF